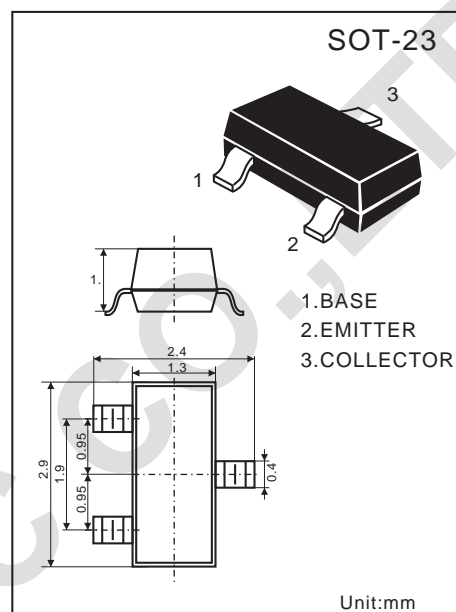


NPN SILICON TRANSISTOR

Features

- Power dissipation
 $P_{CM} : 0.3 \text{ W (} T_{amb}=25^{\circ}\text{C)}$
 - Pulse Drain
 $I_{CM} : 0.1 \text{ mA}$
 - Reverse Voltage
 $V_{(BR)CBO} : \text{BC846 } 80\text{V}$
 - $\text{BC847 } 50\text{V}$
 - $\text{BC848 } 30\text{V}$
- Operating and storage junction temperature range
 $T_j, T_{stg} : -55^{\circ}\text{C to } +150^{\circ}\text{C}$



Electrical Characteristics

($T_a=25^{\circ}\text{C}$)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	BC846 BC847 BC848	$V_{(BR)CBO}$	80 50 30			V
Collector-Emmitter Breakdown Voltage	BC846 BC847 BC848	$V_{(BR)CEO}$	65 45 30			V
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	5			V
Collector Cut-off Current	BC846 BC847 BC848	I_{CBO}			0.1	μA
Collector Cut-off Current	BC846 BC847 BC848	I_{CEO}			0.1	μA
Emitter Cut-off Current		I_{EBO}			0.1	μA
DC Current Gain (Note)	BC846 BC847 BC848	$H_{FE(1)}$	125 220 420		250 475 800	
Collector-Emmitter Saturation Voltage		$V_{CE(sat)}$			0.5	V
Base-emitter saturatio voltage		$V_{BE(sat)}$			1	V
Transition Frequency		f_T	100			MHz

Typical Characteristics

